

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

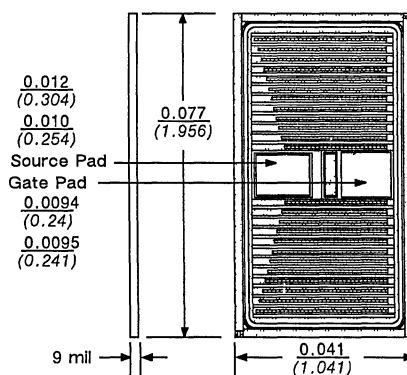
- Switching

FEATURES

- High Speed for Military Applications
(see VNDQ06 for Industrial Applications)

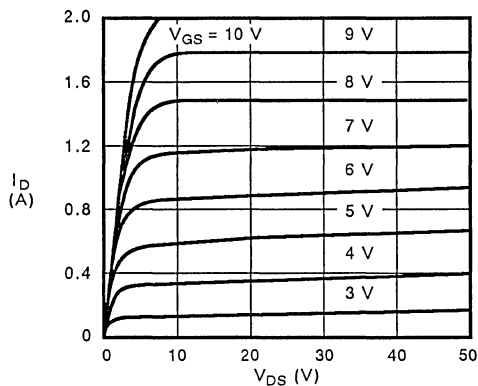
TYPE	PACKAGE	DEVICE
Single	TO-205AD	• JANTX2N6660

GEOMETRY DIAGRAM

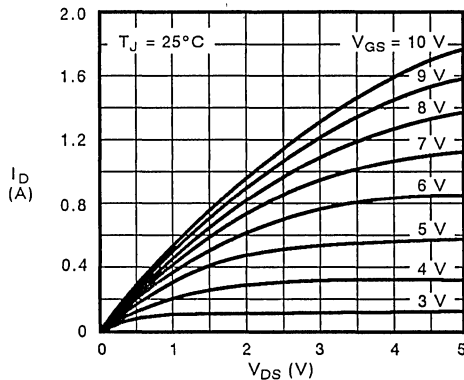


TYPICAL CHARACTERISTICS

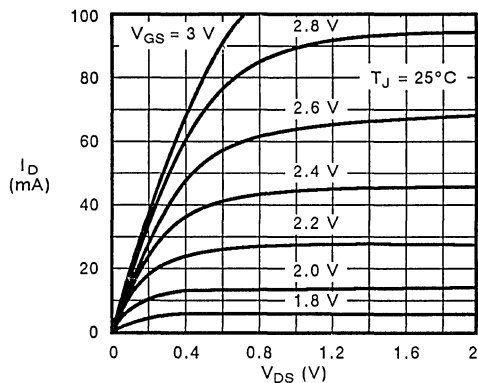
Output Characteristics



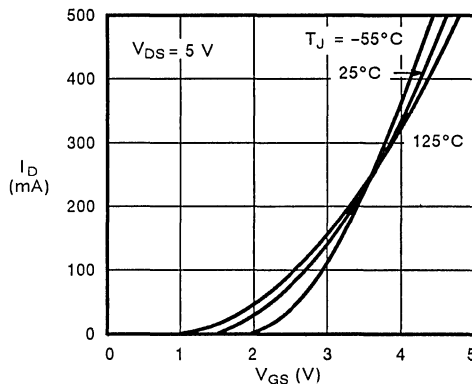
Ohmic Region Characteristics



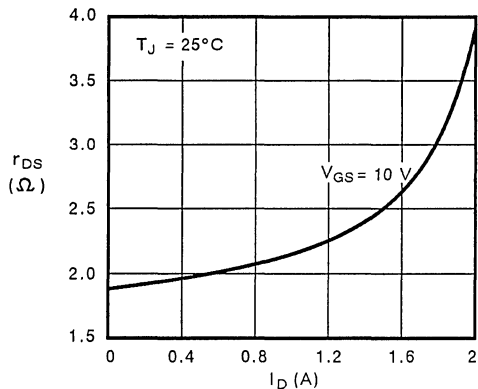
Output Characteristics for Low Gate Drive



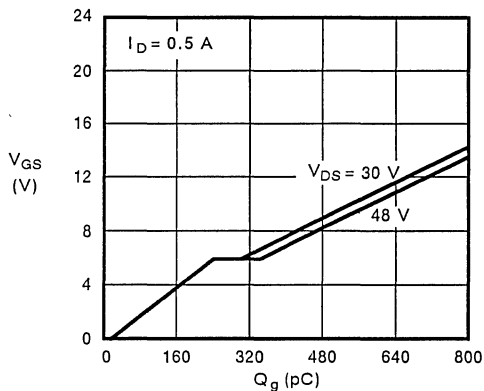
Transfer Characteristics



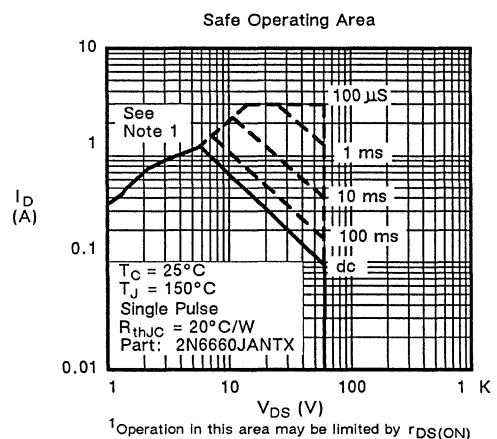
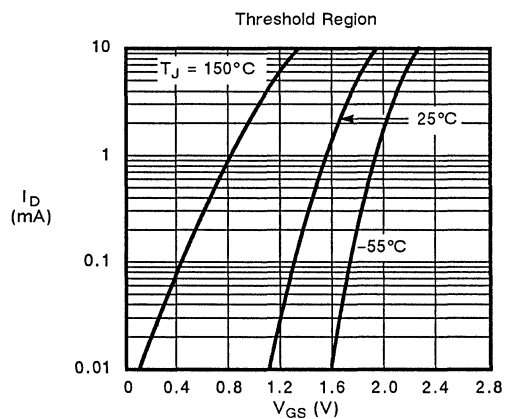
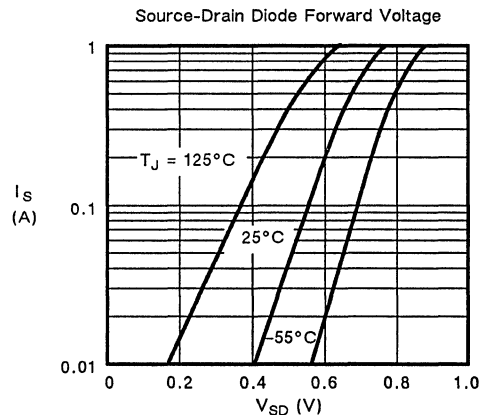
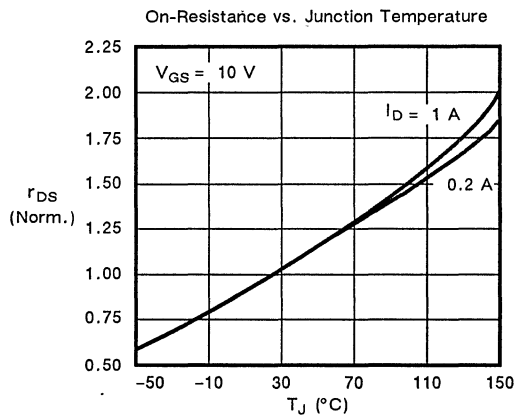
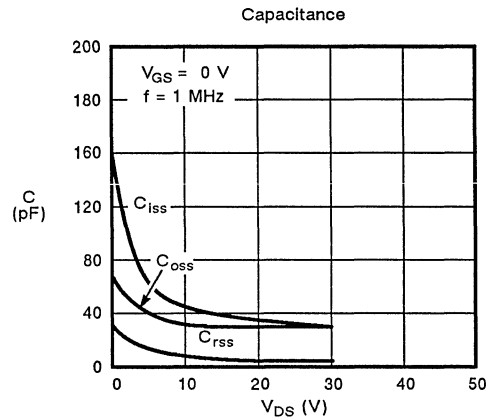
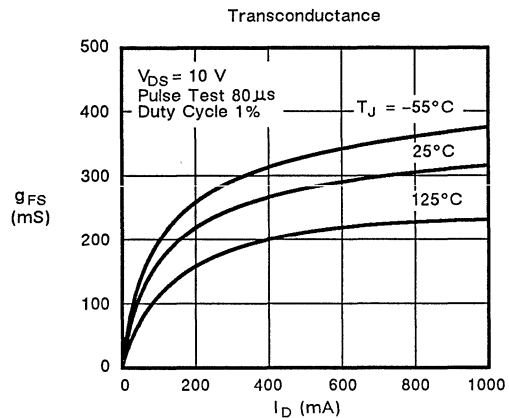
On-Resistance



Gate Charge

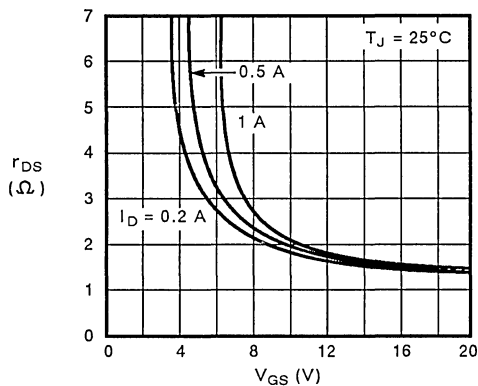


TYPICAL CHARACTERISTICS

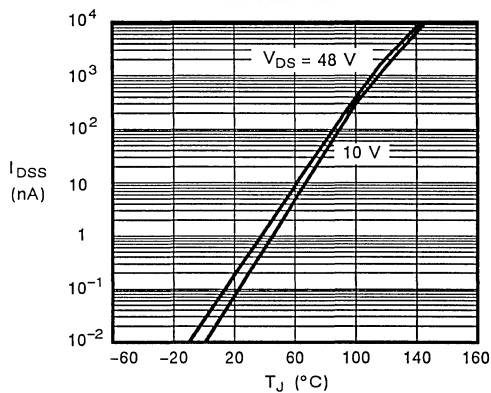


TYPICAL CHARACTERISTICS

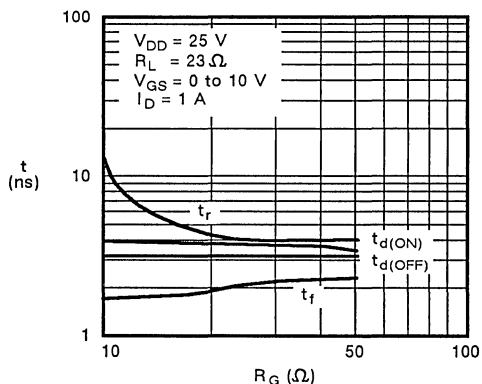
On-Resistance vs. Gate to Source Voltage



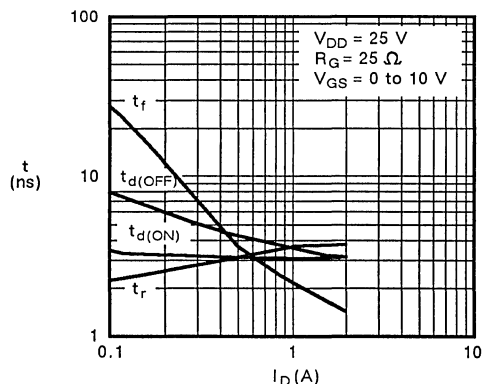
Off State Current



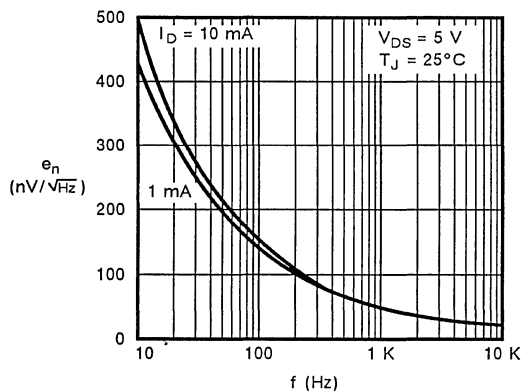
Drive Resistance Effects on Switching



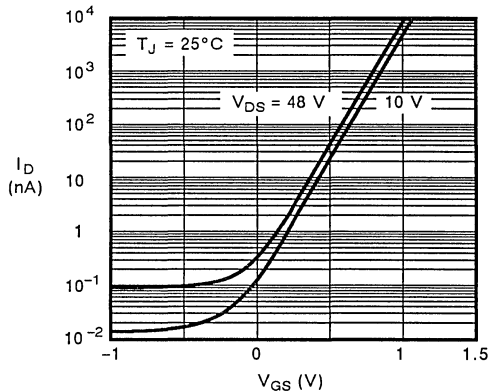
Load Condition Effects on Switching



Equivalent Input Noise Voltage vs. Frequency

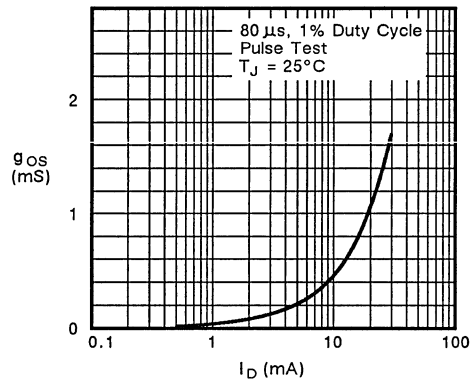


Body-Drain Leakage Current



TYPICAL CHARACTERISTICS

Output Conductance vs. Drain Current



Transient Thermal Response (TO-39)

